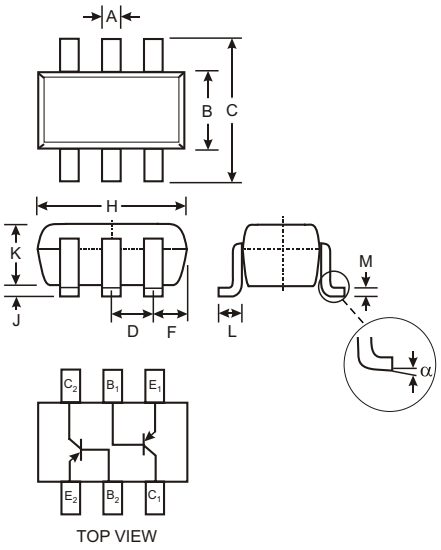
BC857BS

DUAL PNP SURFACE MOUNT SMALL SIGNAL TRANSISTOR

NEW PRODUCT

Features

- Ideally Suited for Automatic Insertion
- For Switching and AF Amplifier Applications
- Ultra-Small Surface Mount Package



SOT-363		
Dim	**Min**	**Max**
A	0.10	0.30
B	1.15	1.35
C	2.00	2.20
D	0.65 Nominal	
F	0.30	0.40
H	1.80	2.20
J	—	0.10
K	0.90	1.00
L	0.25	0.40
M	0.10	0.25
α	0°	8°
All Dimensions in mm		

Mechanical Data

- Case: SOT-363, Molded Plastic
- Case Material - UL Flammability Rating Classification 94V-0
- Moisture sensitivity: Level 1 per J-STD-020A
- Terminals: Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Marking: K3W (See Page 3)
- Weight: 0.006 grams

Maximum Ratings @ T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-50	V
Collector-Emitter Voltage	V_{CEO}	-45	V
Emitter-Base Voltage	V_{EBO}	-5.0	V
Collector Current (Note 1)	I_C	-100	mA
Peak Collector Current (Note 1)	I_{CM}	-200	mA
Peak Base Current (Note 1)	I_{BM}	-200	mA
Power Dissipation at T_{SB} = 50°C (Note 1)	P_d	200	mW
Operating and Storage Temperature Range	T_j, T_{STG}	-55 to +125	°C

Notes: 1. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.

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Electrical Characteristics @ T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
DC Current Gain (Note 2)	h_{FE}	220	—	475	—	V_{CE} = -5.0V, I_C = -2.0mA
Thermal Resistance, Junction to Ambient Air (Note 1)	$R_{\theta JA}$	—	—	625	°C/W	Note 1
Collector-Emitter Saturation Voltage (Note 2)	$V_{CE(SAT)}$	—	— —	-100 -400	mV	I_C = -10mA, I_B = -0.5mA I_C = -100mA, I_B = -5.0mA
Base-Emitter Saturation Voltage (Note 2)	$V_{BE(SAT)}$	—	-700	—	mV	I_C = -10mA, I_B = -0.5mA
Base-Emitter Voltage (Note 2)	V_{BE}	-580	-665	-750	mV	V_{CE} = -5.0V, I_C = -2.0mA
Collector Cutoff Current	I_{CBO} I_{CBO}	—	— —	-15 -4.0	nA µA	V_{CB} = -30V, I_E = 0 V_{CB} = -30V, T_j = 150°C
Emitter Cutoff Current	I_{EBO}	—	—	-100	nA	V_{EB} = -5.0V, I_C = 0
Gain Bandwidth Product	f_T	100	—	—	MHz	V_{CE} = -5.0V, I_C = -10mA, f = 100MHz
Collector-Base Capacitance	C_{CBO}	—	—	3	pF	V_{CB} = -10V, f = 1.0MHz
Emitter-Base Capacitance	C_{EBO}	—	11	—	pF	V_{EB} = -0.5V, f = 1.0MHz

Notes: 1. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.
2. Short duration test pulse used to minimize self-heating effect.

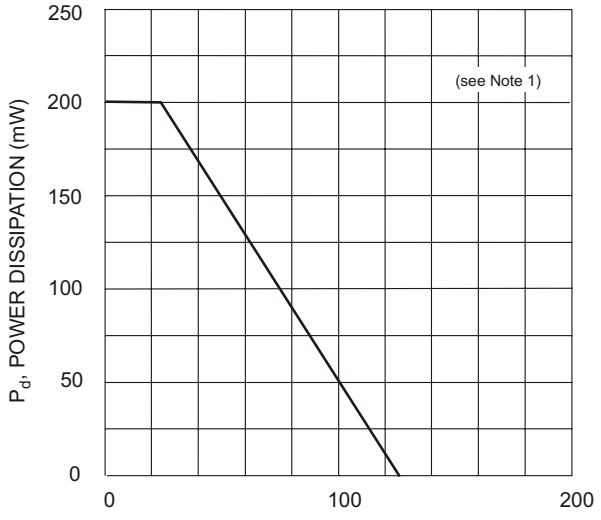

Fig. 1, Power Derating Curve

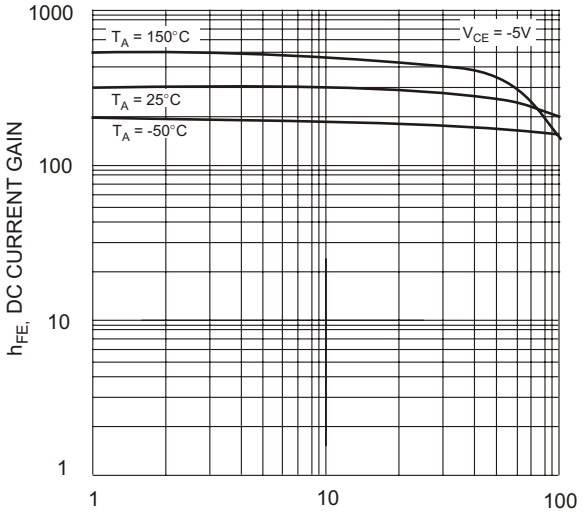

Fig. 2, DC Current Gain vs Collector Current

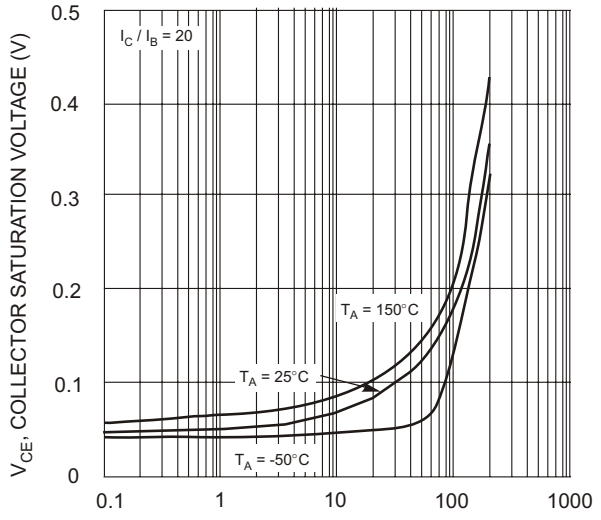

Fig. 3, Collector Saturation Voltage vs Collector Current

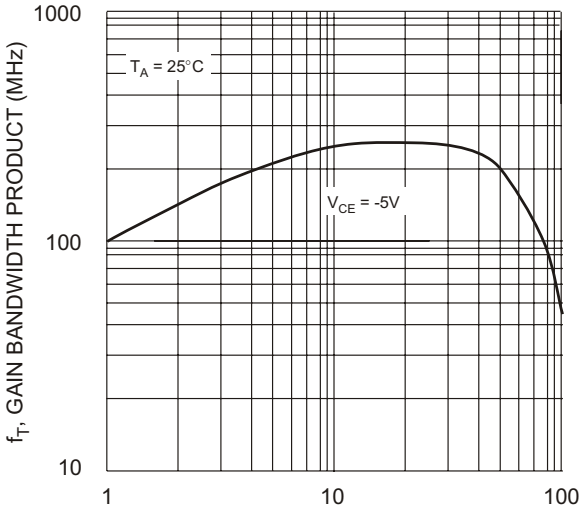

Fig. 4, Gain Bandwidth Product vs Collector Current

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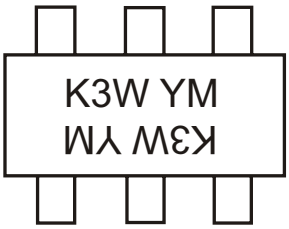
Ordering Information (Note 3)

Device	Packaging	Shipping
BC857BS-7	SOT-363	3000/Tape & Reel

Notes: 3. For Packaging Details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information



K3W = Product Type Marking Code
YM = Date Code Marking
Y = Year ex: N = 2002
M = Month ex: 9 = September

Date Code Key

Year	2002	2003	2004	2005	2006	2007	2008	2009
Code	N	P	R	S	T	U	V	W

Month	Jan	Feb	March	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D